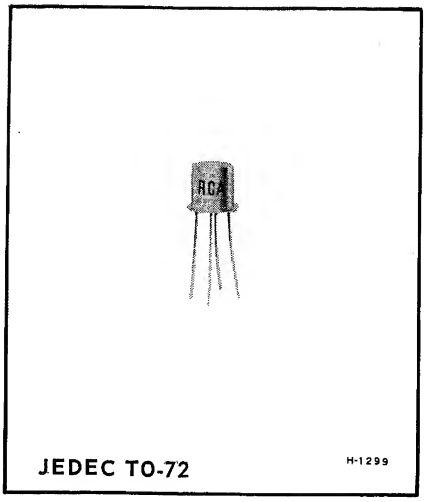


Silicon Dual Insulated-Gate Field-Effect Transistor

With Integrated Gate-Protection Circuits

For Military and Industrial Applications up to 300 MHz

Device Features

- Back-to-back diodes protect each gate against handling and in-circuit transients
- High forward transconductance — g_{fs} = 12,000 μmho (typ.)
- High unneutralized RF power gain — G_{ps} = 18 dB(typ.) at 200 MHz
- Low VHF noise figure — 3.5 dB(typ.) at 200 MHz

RCA-3N187● is an n-channel silicon, depletion type, dual insulated-gate field-effect transistor.

Special back-to-back diodes are diffused directly into the MOS▲ pellet and are electrically connected between each insulated gate and the FET's source. The diodes effectively bypass any voltage transients which exceed approximately ±10 volts. This protects the gates against damage in all normal handling and usage.

A feature of the back-to-back diode configuration is that it allows the 3N187 to retain the wide input signal dynamic range inherent in the MOSFET. In addition, the junction capacitance of these diodes adds little to the total capacitance shunting the signal gate.

The excellent overall performance characteristics of the RCA-3N187 make it useful for a wide variety of rf-amplifier applications at frequencies up to 300 MHz. The two serially-connected channels with independent control gates make possible a greater dynamic range and lower cross-modulation than is normally achieved using devices having only a single control element.

The two-gate arrangement of the 3N187 also makes possible a desirable reduction in feedback capacitance by operating in the common-source configuration and ac-grounding Gate No. 2. The reduced capacitance allows operation at maximum gain *without neutralization;* and, of special importance in rf-amplifiers, it reduces local oscillator feedthrough to the antenna.

The 3N187 is hermetically sealed in the metal JEDEC TO-72 package.

● Formerly developmental type TA7669
▲ Metal-Oxide-Semiconductor

Applications

- RF amplifier, mixer, and IF amplifier in military, and industrial communications equipment
- Aircraft and marine vehicular receivers
- CATV and MATV equipment
- Telemetry and multiplex equipment

Performance Features

- Superior cross-modulation performance and greater dynamic range than bipolar or single-gate FET's
- Wide dynamic range permits large-signal handling before overload
- Virtually no agc power required
- Greatly reduces spurious responses in FM receivers

Maximum Ratings,

Absolute-Maximum Values, at T_A = 25°C

DRAIN-TO-SOURCE VOLTAGE, V_{DS}	-0.2 to +20	V
GATE No. 1-TO-SOURCE VOLTAGE, V_{G1S}:		
Continuous (dc)	-6 to +3	V
Peak ac	-6 to +6	V
GATE No. 2-TO-SOURCE VOLTAGE, V_{G2S}:		
Continuous (dc)	-6 to 30% of V_{DS}	V
Peak ac	-6 to +6	V
*DRAIN-TO-GATE VOLTAGE, V_{DG1} OR V_{DG2}	+20	V
*DRAIN CURRENT, I_D	50	mA
*TRANSISTOR DISSIPATION P_T:		
At ambient temperatures up to 25°C	330	mW
At ambient temperatures above 25°C	derate linearly at 2.2 mW/°C	
*AMBIENT TEMPERATURE RANGE:		
Storage and Operating	-65 to +175	°C
*LEAD TEMPERATURE (During Soldering):		
At distances ≥ 1/32 inch from seating surface for 10 seconds max.	265	°C

*In accordance with JEDEC Registration Data Format JS-9 RDF-19A

3N187 MOSFET for Military and Industrial Applications up to 300 MHz

Information furnished by RCA is believed to be accurate and reliable. However, no responsibility is assumed by RCA for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of RCA.

Printed in U.S.A./5-70

ELECTRICAL CHARACTERISTICS, at T_A = 25° C unless otherwise specified

	CHARACTERISTICS	SYMBOL	TEST CONDITIONS		LIMITS Min.	LIMITS Typ.	LIMITS Max.	UNITS
*	Gate No. 1-to-Source Cutoff Voltage	$V_{G1S(off)}$	V_{DS} = +15 V, I_D = 50 μA V_{G2S} = +4 V		−0.5	−2	−4	V
*	Gate No. 2-to-Source Cutoff Voltage	$V_{G2S(off)}$	V_{DS} = +15 V, I_D = 50 μA V_{G1S} = 0		−0.5	−2	−4	V
*	Gate No. 1-Terminal Forward Current	I_{G1SSF}	V_{G1S} = +1 V $V_{G2S} = V_{DS}$ = 0	T_A = 25° C	–	–	50	nA
				T_A = 100° C	–	–	5	μA
*	Gate No. 1-Terminal Reverse Current	I_{G1SSR}	V_{G1S} = -6 V $V_{G2S} = V_{DS}$=0	T_A = 25° C	–	–	50	nA
				T_A = 100° C	–	–	5	μA
*	Gate No. 2-Terminal Forward Current	I_{G2SSF}	V_{G2S} = +6 V $V_{G1S} = V_{DS}$=0	T_A = 25° C	–	–	50	nA
				T_A = 100° C	–	–	5	μA
*	Gate No. 2-Terminal Reverse Current	I_{G2SSR}	V_{G2S} = -6 V $V_{G1S} = V_{DS}$=0	T_A = 25° C	–	–	50	nA
				T_A = 100° C	–	–	5	μA
*	Zero-Bias Drain Current	I_{DS}	V_{DS} = +15 V V_{G2S} = +4 V V_{G1S} = 0		5	15	30	mA
	Forward Transconductance (Gate No. 1-to-Drain)	g_{fs}	V_{DS} = +15 V, I_D = 10 mA V_{G2S} = +4 V, f = 1 kHz		7000	12,000	18,000	μmho
*	Small-Signal, Short-Circuit Input Capacitance†	C_{iss}	V_{DS} = +15 V, I_D = 10 mA V_{G2S} = +4 V, f = 1 MHz		4.0	6.0	8.5	pF
*	Small-Signal, Short-Circuit, Reverse Transfer Capacitance (Drain-to-Gate No. 1)♦	C_{rss}			0.005	0.02	0.03	pF
*	Small-Signal, Short-Circuit Output Capacitanc	C_{oss}			–	2.0	–	pF
	Power Gain (see Fig. 1)	G_{PS}	V_{DS} = +15 V, I_D = 10 mA V_{G2S} = +4 V, f = 200 MHz		16	18	22	dB
	Maximum Available Power Gain	MAG			–	20	–	dB
	Maximum Usable Power Gain (unneutralized)	MUG			–	20▲	–	dB
	Noise Figure (see Fig. 1)	NF			–	3.5	4.5	dB
*	Magnitude of Forward Transadmittance	$\lvert Y_{fs}\rvert$			–	12,000	–	μmho
*	Phase Angle of Forward Transadmittance	θ			–	−35	–	Degrees
	Magnitude of Reverse Transadmittance	$\lvert Y_{rs}\rvert$			–	25	–	μmho
	Angle of Reverse Transadmittance	θ_{rs}			–	−25	–	Degrees
*	Input Resistance	r_{iss}			–	1.0	–	kΩ
*	Output Resistance	r_{oss}			–	2.8	–	kΩ
*	Gate-to-Source Forward Breakdown Voltage: Gate No. 1	$V_{(BR)G1SSF}$	$I_{G1SSF} = I_{G2SSF}$ = 100 μA		6.5	10	–	V
	Gate No. 2	$V_{(BR)G2SSF}$						
*	Gate-to-Source Reverse Breakdown Voltage: Gate No. 1	$V_{(BR)G1SSR}$	$I_{G1SSR} = I_{G2SSR}$ = -100 μA		−6.5	−10	–	V
	Gate No. 2	$V_{(BR)G2SSR}$						

▲Limited only by practical design considerations.

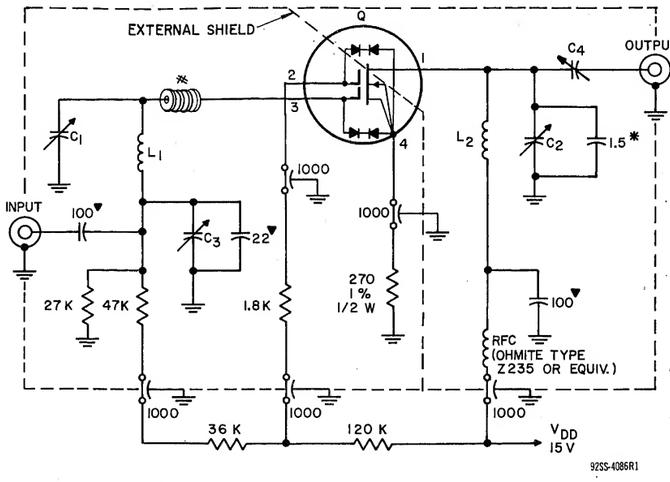
† Capacitance between Gate No. 1 and all other terminals

♦ Three-terminal measurement with Gate No. 2 and Source returned to ground terminal.

* In accordance with JEDEC Registration Data Format JS-9 RDF-19A

OPERATING CONSIDERATIONS

The flexible leads of the 3N187 are usually soldered to circuit elements. As in the case of any high-frequency semiconductor device, the tips of soldering irons MUST be grounded.



Ferrite bead (4); Pyroferric Co. "Carbonyl J" 0.09 in. OD; 0.03 in. ID; 0.063 in. thickness. Q = 3N187 ▼ Disc ceramic. * Tubular ceramic.

All resistors in ohms

All capacitors in pF

C_1: 1.8–8.7 pF variable air capacitor: E.F. Johnson Type 160-104, or equivalent.

C_2: 1.5–5 pF variable air capacitor: E.F. Johnson Type 160-102, or equivalent.

C_3: 1–10 pF piston-type variable air capacitor: JFD Type VAM-010; Johanson Type 4335, or equivalent.

C_4: 0.8–4.5 pF piston type variable air capacitor: Erie 560-013 or equivalent.

L_1: 4 turns silver-plated 0.02-in. thick, 0.075-0.085-in. wide, copper ribbon. Internal diameter of winding = 0.25 in, winding length approx. 0.08 in.

L_2: 4½ turns silver-plated 0.02-in thick, 0.085-0.095-in. wide, 5/16-in. ID. Coil ≈.90 in. long.

Fig. 1 - 200 MHz Power gain and noise figure test circuit

Typical Characteristics

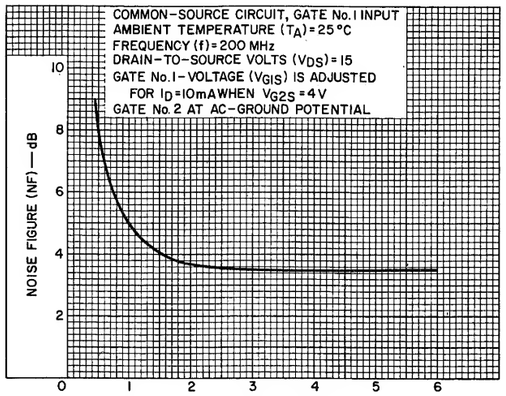


Fig. 2 - NF vs. V_{G2S}

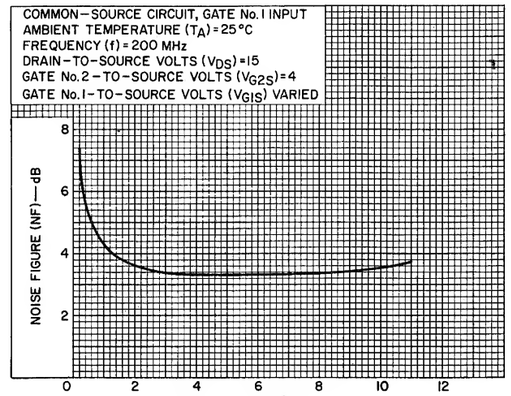


Fig. 3 - NF vs. I_D

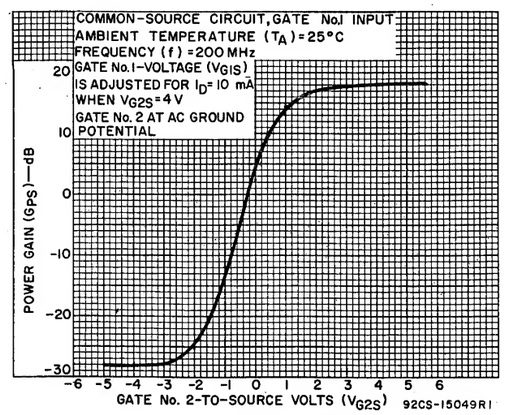


Fig. 4 - G_{PS} vs. V_{G2S}

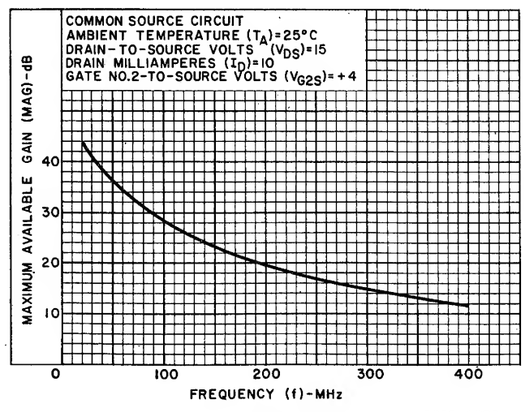


Fig. 5 - MAG. vs. f

Typical Characteristics

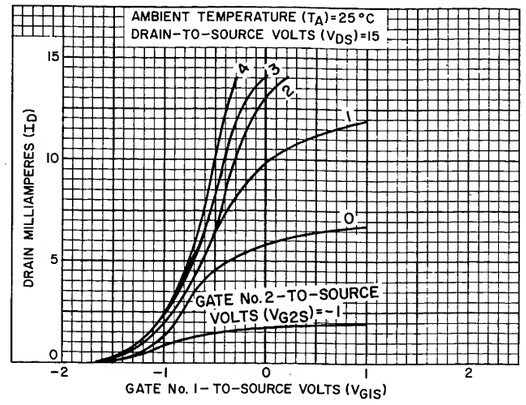


Fig. 6 - I_D vs. V_{G1S}

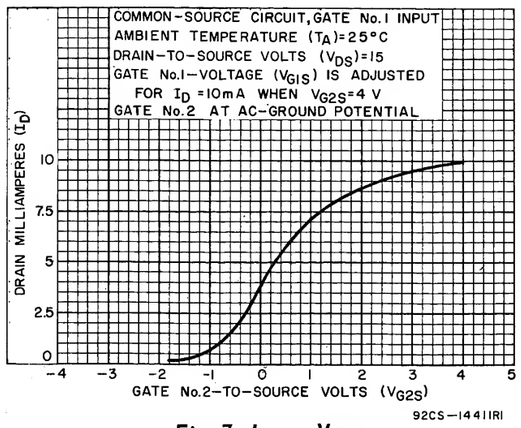


Fig. 7 - I_D vs. V_{G2S}

Typical y Parameters vs. V_{DS}

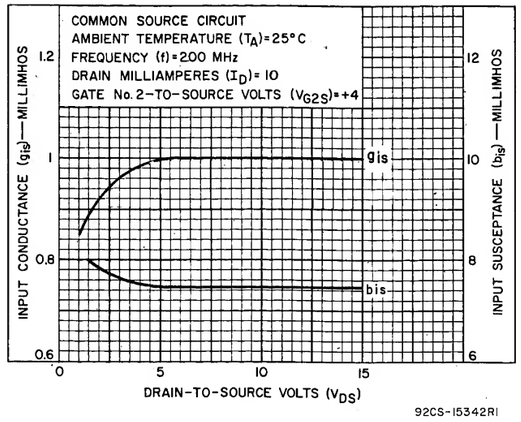


Fig. 8 - y_{is} vs. V_{DS}

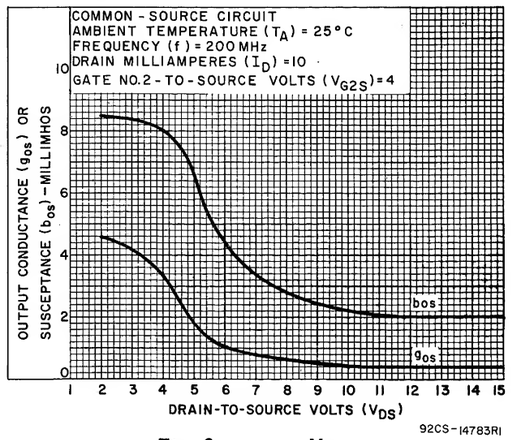


Fig. 9 - y_{os} vs. V_{DS}

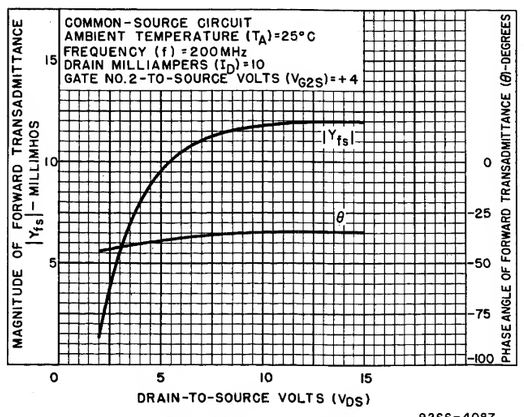


Fig. 10 - y_{fs} vs. V_{DS}

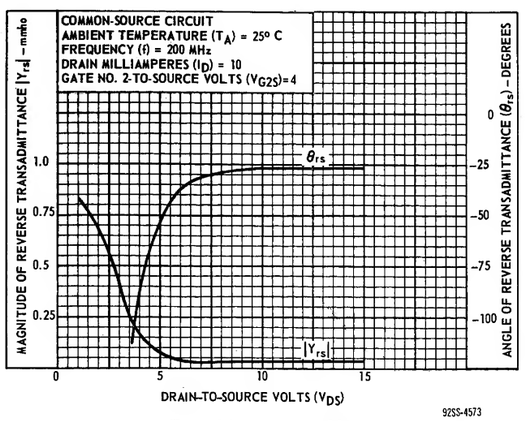


Fig. 11 - y_{rs} vs. V_{DS}

Typical y Parameters vs. I_D

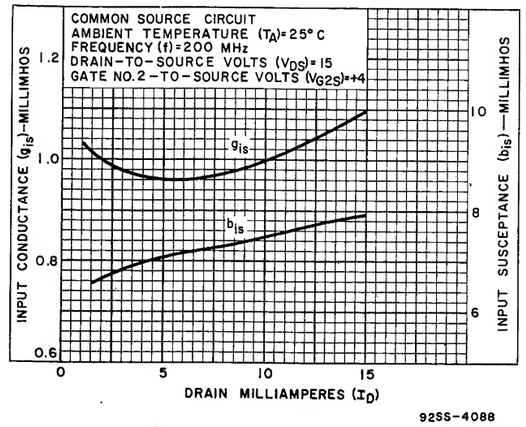


Fig. 12 - y_{is} vs. I_D

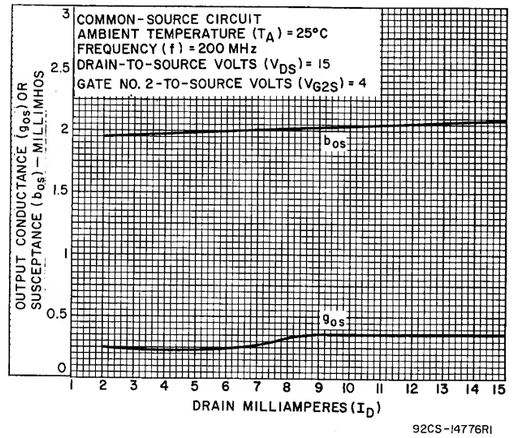


Fig. 13 - y_{os} vs. I_D

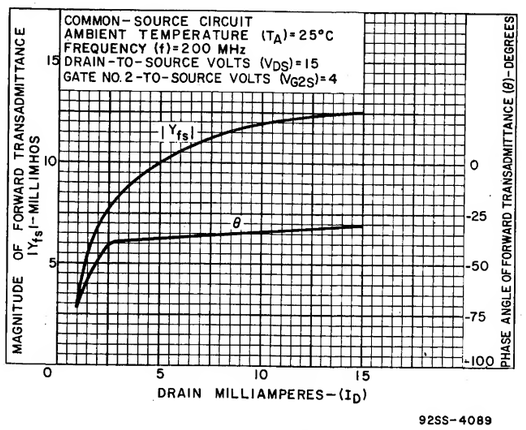


Fig. 14 - y_{fs} vs. I_D

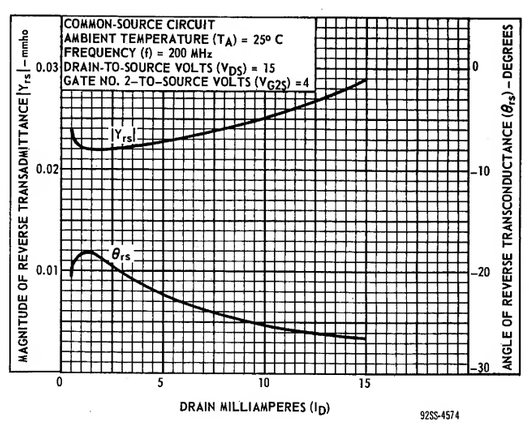


Fig. 15 - y_{rs} vs. I_D

Typical y Parameters vs. V_{G2S}

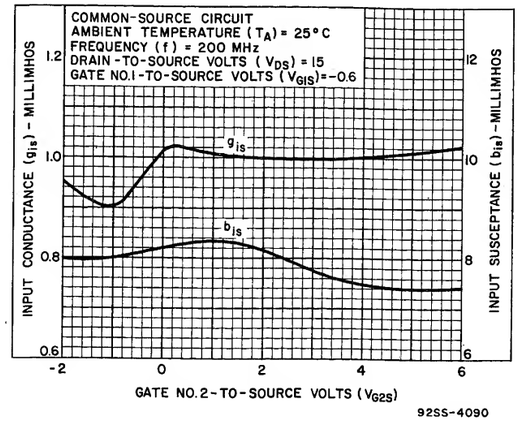


Fig. 16 - y_{is} vs. V_{G2S}

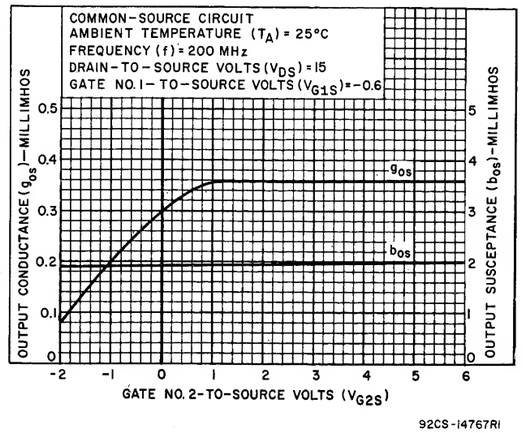


Fig. 17 - y_{os} vs. V_{G2S}

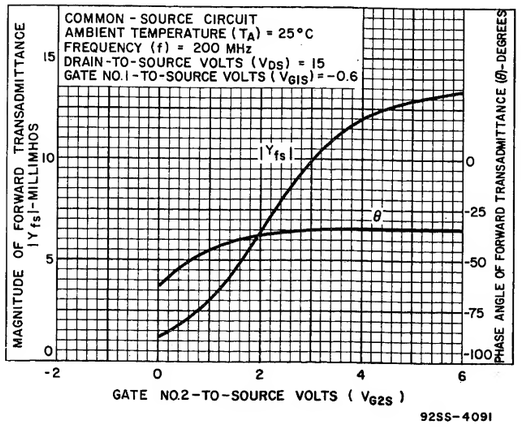


Fig. 18 - y_{fs} vs. V_{G2S}

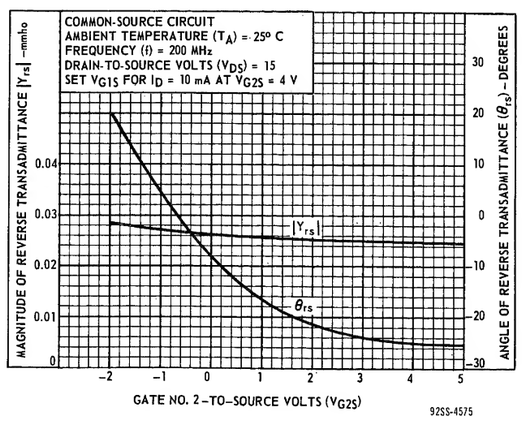


Fig. 19 - y_{rs} vs. V_{G2S}

Typical y Parameters vs. Frequency

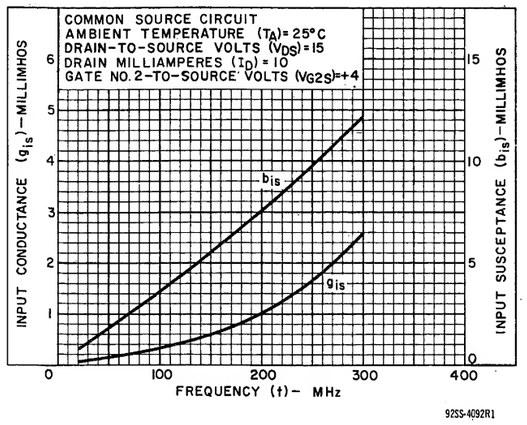


Fig. 20 - y_{is} vs. frequency

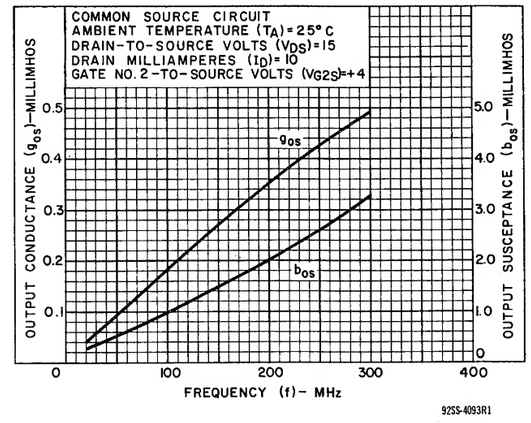


Fig. 21 - y_{os} vs. frequency

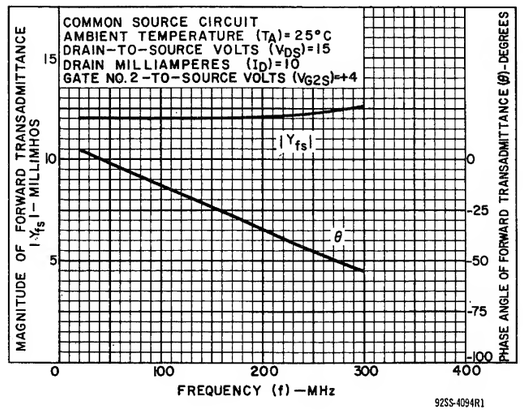


Fig. 22 - y_{fs} vs. frequency

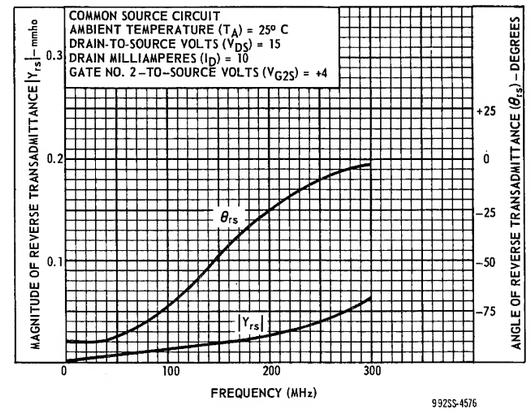


Fig. 23 - y_{rs} vs. frequency

Typical Characteristics

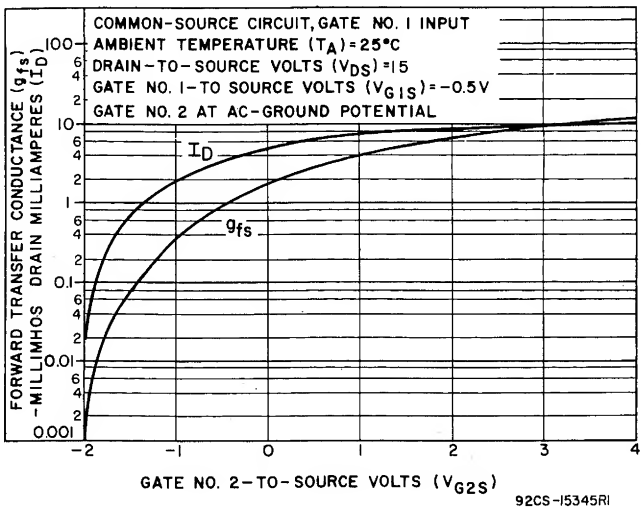


Fig. 24 - g_{fs} and I_D vs. V_{G2S}

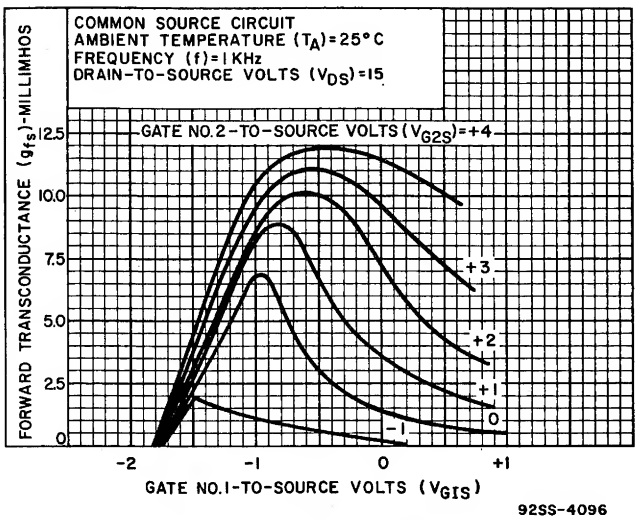


Fig. 25. - g_{fs} vs. V_{G1S}

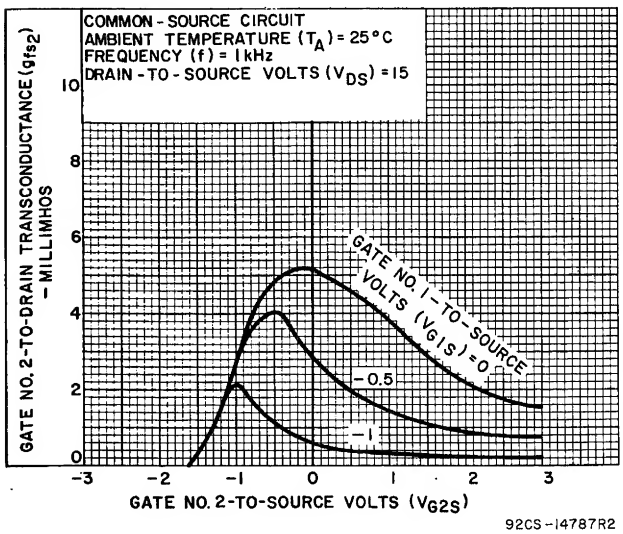
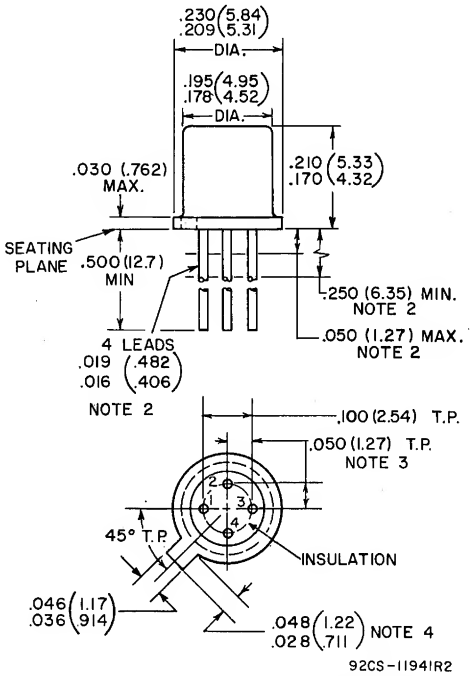


Fig. 26 - g_{fs_2} vs. V_{G2S}

DIMENSIONAL OUTLINE
JEDEC TO-72



Dimensions in Inches and Millimeters

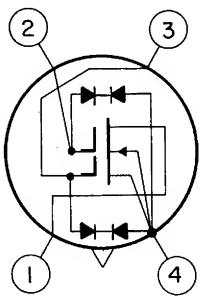
Note 1: *Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated.*

Note 2: The specified lead diameter applies in the zone between 0.050" (1.27 mm) and 0.250" (6.35 mm) from the seating plane. From 0.250" (6.35 mm) to the end of the lead a maximum diameter of 0.021" (0.533 mm) is held. Outside of these zones, the lead diameter is not controlled.

Note 3: Leads having a maximum diameter of 0.019" (0.482 mm) at a guaging plane of 0.054" (1.372 mm) + 0.001" (0.025 mm) -0.000" (0.000 mm) below seating plane shall be within 0.007" (0.177 mm) at their true position (location) relative to a maximum width of tab.

Note 4: Measured from actual maximum diameter.

TERMINAL DIAGRAM



LEAD 1 - DRAIN
LEAD 2 - GATE No. 2
LEAD 3 - GATE No. 1
LEAD 4 - SOURCE, SUBSTRATE AND CASE